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Memory Products	

82S126A 82S129A

1K-bit TTL bipolar PROM

DESCRIPTION

The 82S126A and 82S129A are field programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The 82S126A and 82S129A devices are supplied with all outputs at logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

These devices include on-chip decoding and 2 Chip Enable inputs for ease of memory expansion. They feature either Open Collector or 3-State outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

The 82S126A and 82S129A devices are also processed to military requirements for operation over the military temperature range. For specifications and ordering information, consult the Signetics Military Data Handbook.

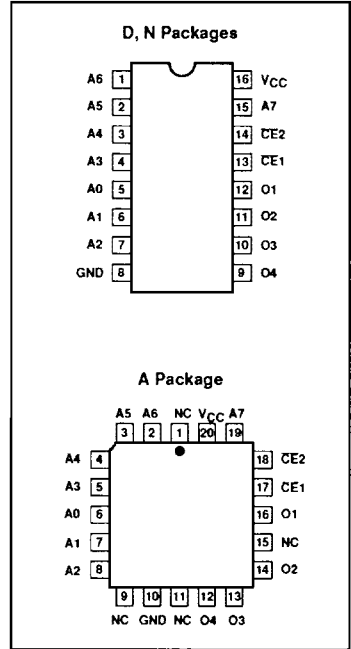
FEATURES

- Address access time:
 - N82S126A: 30ns max
 - N82S129A: 27ns max
- Power dissipation: 0.5mW/bit typ
- Input loading: –100µA max
- On-chip address decoding
- Two Chip Enable inputs
- Output options:
 - N82S126A: Open Collector
 - N82S129A: 3-State
- No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible

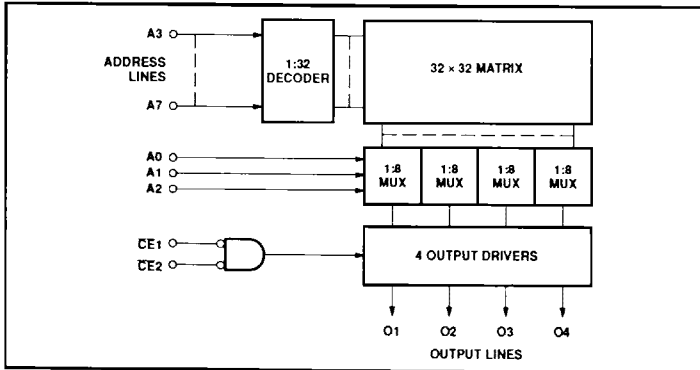
APPLICATIONS

- Prototyping/volume production
- Sequential controllers
- Format conversion
- Hardwired algorithms
- Random logic
- Code conversion

PIN CONFIGURATIONS



BLOCK DIAGRAM



1K-bit TTL bipolar PROM (256 × 4)

82S126A / 82S129A

ORDERING INFORMATION

DESCRIPTION	ORDER CODE
16-Pin Plastic Dual-In-Line 300mil-wide	N82S126A N, N82S129A N
16-Pin Plastic SO 300mil-wide	N82S126A D, N82S129A D
20-Pin Plastic Leaded Chip Carrier 350mil-square	N82S126A A, N82S129A A

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	+7.0	V _{DC}
V _{IN}	Input voltage	+5.5	V _{DC}
V _{O-H}	Output voltage High (82S126A)	+5.5	V _{DC}
V _O	Output voltage Off-State (82S129A)	+5.5	V _{DC}
T _{amb}	Operating temperature range	0 to +75	°C
T _{stg}	Storage temperature range	-65 to +150	°C

DC ELECTRICAL CHARACTERISTICS

0 °C ≤ T_{amb} ≤ +75 °C, 4.75V ≤ V_{CC} ≤ 5.25V

SYMBOL	PARAMETER	TEST CONDITIONS ^{1,2}	LIMITS			UNIT
			MIN	TYP ³	MAX	
Input voltage						
V _{IL}	Low	V _{CC} = 4.75V	2.0		0.8	V
V _{IH}	High	V _{CC} = 5.25V			V	
V _C	Clamp	V _{CC} = 4.75V, I _{IN} = -12mA			-1.2	V
Output voltage						
V _{OL}	Low	CE1,2 = Low I _{OUT} = 16mA	2.4		0.45	V
V _{O-H}	High (82S129A)	I _{OUT} = -2.0mA			V	
Input current						
I _{IL}	Low	V _{IN} = 0.45V			-100	μA
I _{IH}	High	V _{IN} = 5.5V			40	μA
Output current						
I _{OLK}	Leakage (82S126A)	CE1 or CE2 = High, V _{OUT} = 5.5V			40	μA
I _{OZ}	Hi-Z state (82S129A)	CE1 or CE2 = High, V _{OUT} = 5.5V			40	μA
I _{OS}	Short circuit (82S129A) ⁴	CE1 or CE2 = High, V _{OUT} = 0.5V			-40	μA
		CE1,2 = Low, V _{OUT} = 0V, High stored	-15		-70	mA
Supply current⁵						
I _{CC}		V _{CC} = 5.25V			120	mA
Capacitance						
C _{IN}	Input	CE1 or CE2 = High, V _{CC} = 5.0V V _{IN} = 2.0V		5		pF
C _{OUT}	Output	V _{OUT} = 2.0V		8		pF

NOTES:

- Positive current is defined as into the terminal referenced.
- All voltages with respect to network ground.
- Typical values are at V_{CC} = 5V, T_{amb} = +25°C.
- Duration of short circuit should not exceed 1 second.
- Measured with all inputs grounded and all outputs open.

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82S126A / 82S129A

AC ELECTRICAL CHARACTERISTICS

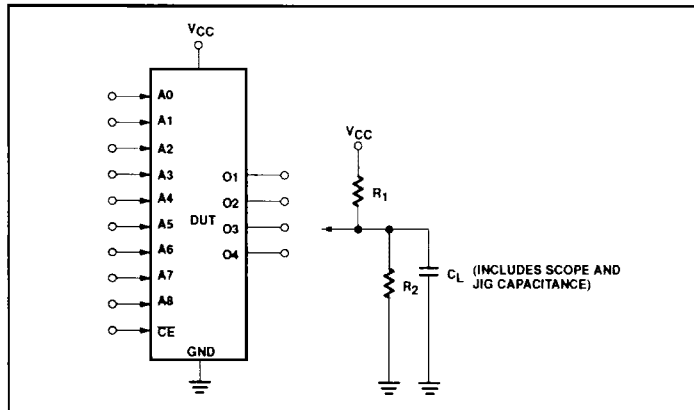
$R_1 = 270\Omega$, $R_2 = 600\Omega$, $C_L = 30\text{pF}$, $0^\circ\text{C} \leq T_{\text{amb}} \leq +75^\circ\text{C}$, $4.75\text{V} \leq V_{\text{CC}} \leq 5.25\text{V}$

SYMBOL	PARAMETER	TO	FROM	N82S129A			N82S126A			UNIT
				MIN	TYP ¹	MAX	MIN	TYP ¹	MAX	
Access time²										
t_{AA}		Output	Address		17	27		17	30	ns
t_{CE}		Output	Chip Enable		10	20		10	20	ns
Disable time³										
t_{CD}		Output	Chip Enable		6	15		6	15	ns

NOTES:

1. Typical values are $V_{\text{CC}} = 5\text{V}$, $T_{\text{amb}} = +25^\circ\text{C}$.
2. Tested at an address cycle time of $1\mu\text{s}$.
3. Measured at a delta of 0.5V from Logic Level with $R_1 = 750\Omega$, $R_2 = 750\Omega$ and $C_L = 5\text{pF}$.

TEST LOAD CIRCUIT



VOLTAGE WAVEFORMS

